



Line 18, change "radiating" to --receiving--.

Page 13

Line 18, change "being remained" to --remaining--.

Line 22, delete "the" (first occurrence).

Page 14

Line 1, delete "the" (first occurrence).

Line 2, change "wring" to --wiring--.

Line 11, delete "the" (first occurrence).

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In the Claims

Please cancel claims 1-8, without prejudice. Claims 1-7 have been rewritten as the new claims. Claim 8 has been withdrawn as being directed to a non-elected invention and a divisional application may be filed.

Please add claims 9-14, as follows:

9. (New) A semiconductor device comprising:
 - a substrate having a region irradiated with radiating rays,
 - crystal defects within the region irradiated, and
 - a metal wiring layer located over the substrate, the metal wiring layer being made of a light metal, the metal wiring layer having an opening above the region irradiated, so that radiating rays passing to the region irradiated through the opening generate the crystal defects within the region irradiated.
10. (New) The semiconductor device in accordance with Claim 9, wherein the metal wiring layer is formed in a thickness so as to restrict penetration of the radiating rays into the region irradiated.
11. (New) The semiconductor device in accordance with Claim 10, wherein an insulating layer is formed above the region irradiated, the opening being on the insulating layer.